

Description

The WPE3V3D3ULA is a 5V bi-directional TVS diode. utilizing leading monolithic silicon technology to provide fast re-sponse time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive high-speed data lines. WPE3V3D3ULA has a low capaci-tance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make WPE3V3D3ULA an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

• 360W peak pulse power (8/20µs)

Ultra low capacitance: 1pF typical

Ultra low leakage: nA level

Operating voltage: 3.3V

Low clamping voltage

Protects one power line or data line

Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 21A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: SOD-323

• Lead Finish: Matte Tin

• Case Material: "Green" Molding Compound.

• Moisture Sensitivity: Level 3 per J-STD-020

Terminal Connections: See Diagram Below

Marking Information: See Below

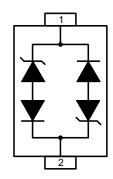
Applications

- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information



Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
WPE3V3D3ULA	3000	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

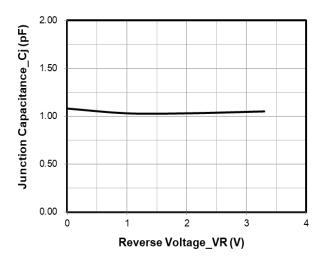
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	350	W
Peak Pulse Current (8/20µs)	IPP	21	А
ESD per IEC 61000-4-2 (Air)	\/50p	±30	141
ESD per IEC 61000-4-2 (Contact)	VESD	±30	kV
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

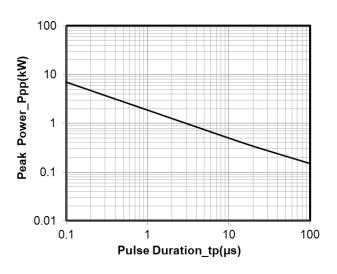
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Punch-Through Voltage	VPT	3.5			V	Iτ = 2μA
Snap-Back Voltage	VBR	2.8			V	IT = 50mA
Reverse Leakage Current	I _R			0.2	μA	VRWM = 3.3V
Clamping Voltage	Vc			5	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			16	V	IPP = 21A (8 x 20µs pulse)
Junction Capacitance	CJ		8.0	1.5	pF	VR = 0V, f = 1MHz

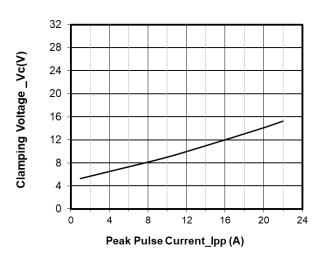


Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

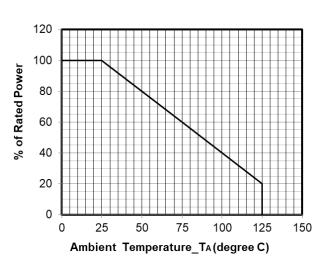




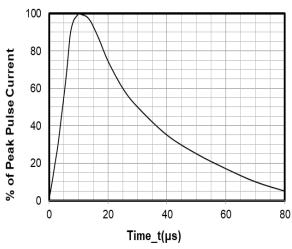
Junction Capacitance vs. Reverse Voltage



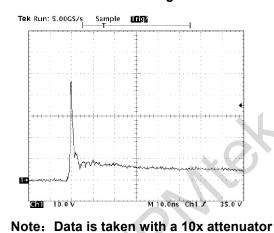
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



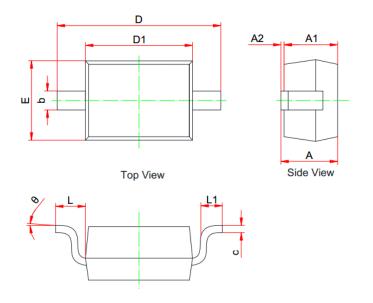
ESD Clamping Voltage

8 kV Contact per IEC61000-4-2

8 X 20µs Pulse Waveform



SOD-323 Package Outline Drawing



	MILLIMETERS				
SYM	MIN	NOM	MAX		
Α	0.800		1.100		
A1	0.800		0.900		
A2	0.000		0.100		
b	0.250		0.400		
С	0.080		0.177		
D1	1.600	1.700	1.800		
D	2.300		2.800		
E	1.150		1.400		
L	0.475REF				
L1	0.100		0.500		
Θ	0°		8°		

Suggested Land Pattern



Unit: mm

WPMtek reserves the right to make changes to the product specification and data in this document without notice. WPMtek makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does WPMtek assume any liability arising from the application or use of any products or circuits, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Any enquiry please write to sales@wpmtek.com for futher information.